

Integrated Device Technology, Inc.

# 256KB AND 512KB SECONDARY CACHE MODULES FOR THE INTEL® PENTIUM™ PROCESSOR

PRELIMINARY  
IDT7MPV6179  
IDT7MPV6189  
IDT7MP6181  
IDT7MP6182

## FEATURES

- 256KB, 512KB 3.3V I/O compatible secondary cache module family
- Ideal for use with many Intel Pentium CPU-based systems, especially those using the Intel 82430NX (Neptune) PCiset
- Separate 3.3V and 5V power supplies
- Operates with Pentium processor external bus speeds of 66MHz
- Low-cost, low-profile cardedge module with 160 leads
- Uses Burndy Computerbus™ connector, part number CELP2X80SC3Z48
- Multiple GND pins and decoupling capacitors for maximum noise immunity

## DESCRIPTION

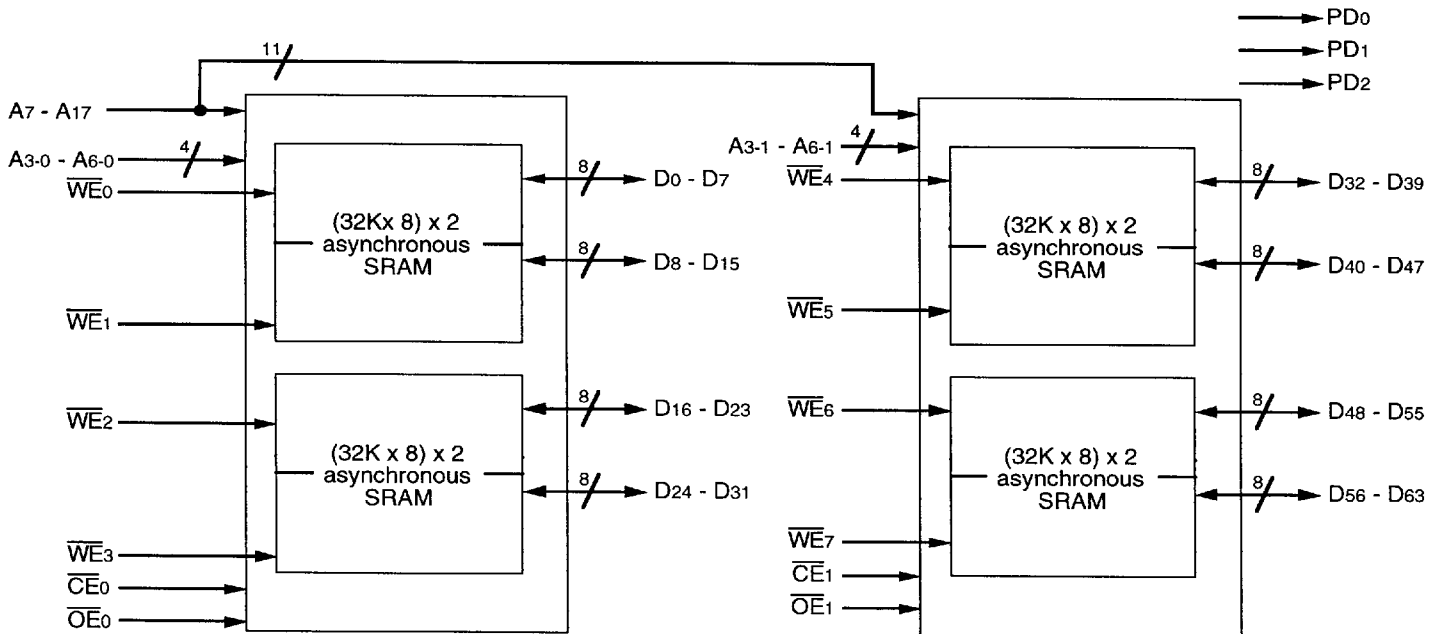
The IDT7MPV6179/89 and IDT7MP6181/82 are a family of 256KB and 512KB secondary caches that are ideal for use with many Intel Pentium CPU-based systems, especially those using the Intel 82430NX (Neptune) PCiset. The

IDT7MPV6179/89 and IDT7MP6181/82 use asynchronous and burst CacheRAMs™ respectively in plastic surface mount packages mounted on a multilayer epoxy laminate (FR-4) board. Extremely high speeds are achieved using IDT's high-performance, high-reliability BiCMOS and CMOS technologies. The IDT7MPV6189 is a latched address asynchronous SRAM version of the IDT7MP6179 which saves the designer a latch on the motherboard as well as giving the opportunity to further improve performance with the use of the IDT7MP6181/82 burst SRAMs module versions.

The low-profile cardedge package configuration allows 160 signal leads to be placed on a package 4.35" long. Depending on which cache configuration is used, the module is a maximum of 0.445" thick and a maximum of 1.15" tall.

All inputs and outputs of the IDT7MPV6179/89 and IDT7MP6181/82 are TTL-compatible, and operate from separate 3.3V power supplies for the asynchronous SRAM versions and 5.0V for the burst cache SRAM versions. Burst SRAM versions are 3.3V I/O compatible. Equal clock line trace lengths ensure minimum clock skew. Multiple GND pins and on-board decoupling capacitors ensure maximum protection from noise.

## FUNCTIONAL BLOCK DIAGRAM IDT7MPV6179



3058 drw 01

The IDT logo is a registered trademark and CacheRAM is a trademark of Integrated Device Technology, Inc. All others are trademarks of their respective companies.

## COMMERCIAL TEMPERATURE RANGE

FEBRUARY 1995

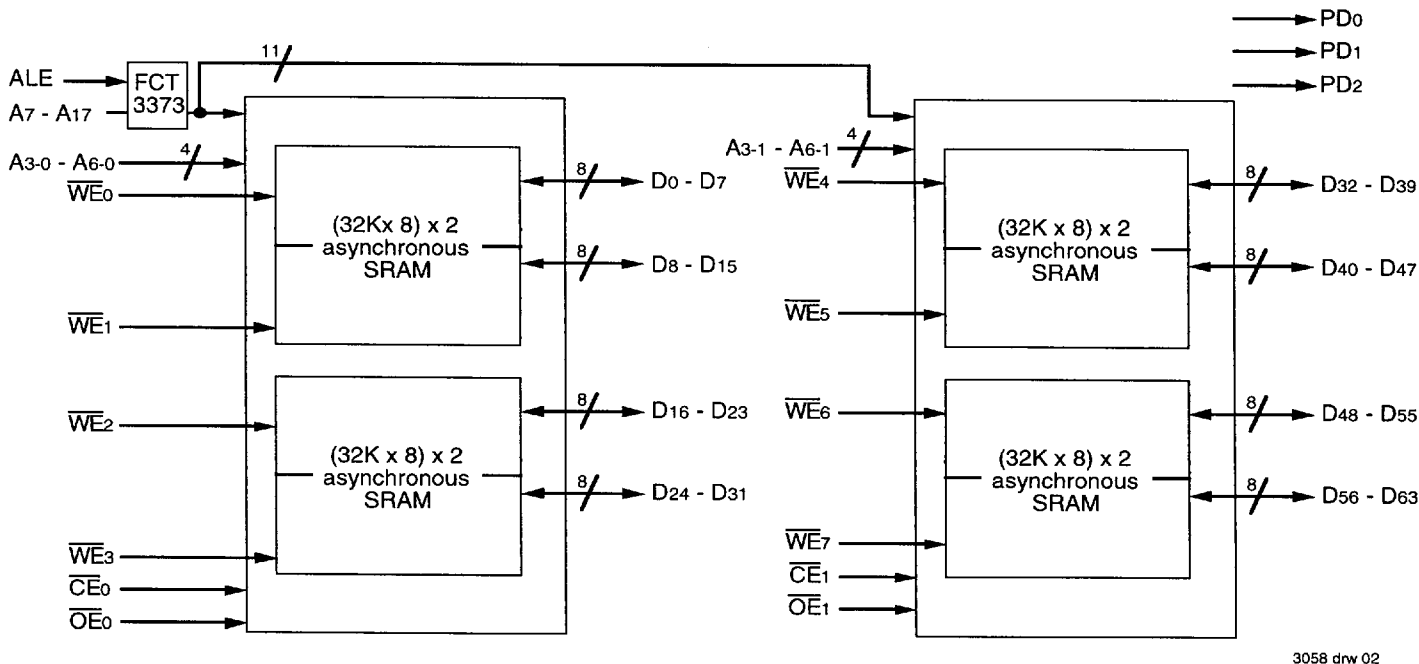
©1994 Integrated Device Technology, Inc.

DSC-7112/2

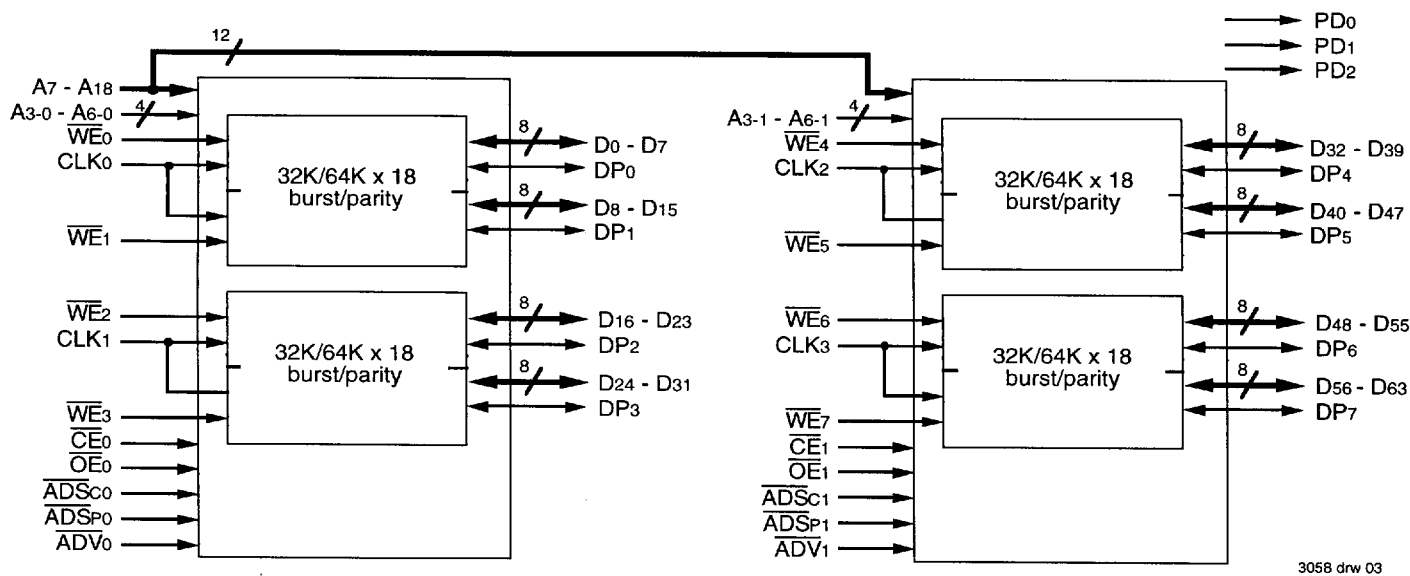
■ 4825771 0021703 849 ■

1

**FUNCTIONAL BLOCK DIAGRAM**  
**IDT7MPV6189**



**IDT7MP6181/82**



**PIN CONFIGURATION<sup>(3)</sup>**

GND	81	1	GND
D63	82	2	D62
VCC5	83	3	VCC3
D61	84	4	D60
VCC5	85	5	VCC3
D59	86	6	D58
D57	87	7	D56
GND	88	8	GND
(1) DP7	89	9	DP6 <sup>(1)</sup>
D55	90	10	D54
D53	91	11	D52
D51	92	12	D50
GND	93	13	GND
D49	94	14	D48
D47	95	15	D46
D45	96	16	D44
D43	97	17	D42
GND	98	18	GND
D41	99	19	D40
(1) DP5	100	20	DP4 <sup>(1)</sup>
D39	101	21	D38
D37	102	22	D36
D35	103	23	D34
GND	104	24	GND
D33	105	25	D32
D31	106	26	D30
D29	107	27	D28
D27	108	28	D26
D25	109	29	D24
GND	110	30	GND
(1) DP3	111	31	DP2 <sup>(1)</sup>
D23	112	32	D22
D21	113	33	D20
VCC5	114	34	VCC3
D19	115	35	D18
GND	116	36	GND
D17	117	37	D16
VCC5	118	38	VCC3
D15	119	39	D14
D13	120	40	D12
GND	121	41	GND
D11	122	42	D10
VCC5	123	43	VCC3
D9	124	44	D8
(1) DP1	125	45	DP0 <sup>(1)</sup>
VCC5	126	46	VCC3
D7	127	47	D6
D5	128	48	D4
D3	129	49	D2
D1	130	50	D0
GND	131	51	GND
A3-1	132	52	A3-0
A4-1	133	53	A4-0
A5-1	134	54	A5-0
A6-1	135	55	A6-0
A7	136	56	A8
GND	137	57	GND
A9	138	58	A10
A11	139	59	A12
A13	140	60	A14
A15	141	61	A16
A17	142	62	A18
GND	143	63	GND
(2)ALE	144	64	PD0
PD1	145	65	PD2
(1)CLK0	146	66	CLK1 <sup>(1)</sup>
(1)CLK2	147	67	CLK3 <sup>(1)</sup>
GND	148	68	GND
WE7	149	69	WE8
WE5	150	70	WE4
WE3	151	71	WE2
WE1	152	72	WE0
GND	153	73	GND
(1)ADSC1	154	74	ADSC0 <sup>(1)</sup>
CE1	155	75	CE0
(1)ADV1	156	76	ADV0 <sup>(1)</sup>
OE1	167	77	OE0
VCC5	158	78	VCC3
(1)ADSP1	159	79	ADSP0 <sup>(1)</sup>
GND	160	80	GND

3058 drw 04

**LOW PROFILE CARDEDGE MODULE  
TOP VIEW**

**NOTES:**

1. These pins are no connects for the asynchronous module versions.
2. This pin is a no connect for all modules but the IDT7MPV6189.
3. Vcc3 is connected only to the asynchronous SRAMs for the IDT7MP6179/89 and Vcc5 is connected to only the burst cache SRAMs for the IDT7MP6181/82.

**PIN NAMES**

A3 – A18	Address Inputs
ALE	Address Latch Enable Input
D0 – D63	Inputs/Outputs
DP0 – DP7	Parity Inputs/Outputs
CE0 – CE1	Chip Enable Inputs
WE0 – WE7	Byte Write Enable Inputs
OE0 – OE1	Output Enable Inputs
ADSP0 – ADSP1	Address Status Processor Inputs
ADSC0 – ADSC1	Address Status Cache Controller Inputs
ADV0 – ADV1	Burst Address Advance Inputs
CLK0 – CLK3	Clock Inputs
PD0 – PD2	Presence Detect Pins
N.C.	No Connect
GND	Ground
Vcc3	Power Supply for Asynchronous SRAMs only
Vcc5	Power Supply for Burst Cache SRAMs only

3058 tbl 01

**PRESENCE DETECT TABLE<sup>(1)</sup>**

PD2	PD1	PD0	SRAM	Type	Size	Module
N.C.	N.C.	N.C.	—	—	—	No cache present
N.C.	N.C.	GND	—	—	—	Reserved
N.C.	GND	N.C.	71V256	Asynch	256KB	IDT7MPV6179/89
N.C.	GND	GND	—	—	—	Reserved
GND	N.C.	N.C.	—	—	—	Reserved
GND	N.C.	GND	—	—	—	Reserved
GND	GND	N.C.	71420	Burst	256KB	IDT7MP6181
GND	GND	GND	64K x 18	Burst	512KB	IDT7MP6182

**NOTE:**

1. The IDT71V256 is the 3.3V 32K x 8 SRAM. The IDT71420 and IDT71620 are respectively 32K x 18 and 64K x 18 burst cache SRAMs which operate from a 5V supply, but are compatible in a 3.3V environment.

3058 tbl 02

**CAPACITANCE<sup>(1, 2)</sup>**

(TA = +25°C, f = 1.0 MHz)

Symbol	Parameter <sup>(1)</sup>	Condition	'6179/89	'6181/2	Unit
CIN1	Input Capacitance (Address)	VIN = 0V	45/10	25	pF
CIN2	Input Capacitance (CE, OE, Control)	VIN = 0V	25	15	pF
CIN3	Input Capacitance (WE, CLK)	VIN = 0V	8	8	pF
Ci/O	I/O Capacitance	VOUT = 0V	10	10	pF

**NOTES:**

1. These parameters are guaranteed by design but not tested.
2. These parameters are maximum values.

3058 tbl 03

4825771 0021705 611

### ABSOLUTE MAXIMUM RATINGS

Symbol	Rating	Value	Unit
VTERM	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
TA	Operating Temperature	0 to +70	°C
TBIAS	Temperature Under Bias	-10 to +85	°C
TSTG	Storage Temperature	-55 to +125	°C
IOUT	DC Output Current	50	mA

**NOTE:**  
 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

3058 tbl 04

### RECOMMENDED DC OPERATING CONDITIONS

Symbol	Parameter	Min.	Typ.	Max.	Unit
Vcc5	Supply Voltage	4.75	5.0	5.25	V
Vcc3	Supply Voltage	3.0	3.3	3.6	V
GND	Supply Voltage	0	0	0.0	V
V <sub>IH</sub>	Input High Voltage	2.2	—	V <sub>cc</sub> + 0.3	V
V <sub>IL</sub>	Input Low Voltage	-0.5 <sup>(1)</sup>	—	0.8	V

**NOTE:**  
 1. V<sub>IL</sub> = -1.0V for pulse width less than 5ns, once per cycle.

3058 tbl 05

### RECOMMENDED OPERATING TEMPERATURE AND SUPPLY VOLTAGE

Module	Ambient Temperature	GND	Vcc
7MP6179/89	0°C to +70°C	0V	3.3V ± 10%
7MP6181/82	0°C to +70°C	0V	5.0V ± 5%

3058 tbl 06

### DC ELECTRICAL CHARACTERISTICS

(V<sub>cc</sub> = 3.3V ± 10% for the 7MPV6179/89, V<sub>cc</sub> = 5.0V ± 5% for the 7MP6181/82 TA = 0°C to 70°C)

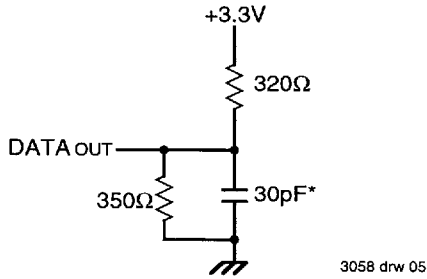
Symbol	Parameter	Test Condition	7MPV6179/89		7MP6181/82		Unit
			Min.	Max.	Min.	Max.	
I <sub>LIL</sub>	Input Leakage Current (Address)	V <sub>cc</sub> = Max, V <sub>IN</sub> = GND to V <sub>cc</sub>	—	20/5	—	40	μA
I <sub>LIL</sub>	Input Leakage Current ( $\overline{CE}$ , $\overline{OE}$ , Control)	V <sub>cc</sub> = Max, V <sub>IN</sub> = GND to V <sub>cc</sub>	—	10	—	20	μA
I <sub>LIL</sub>	Input Leakage Current ( $\overline{WE}$ , CLK)	V <sub>cc</sub> = Max, V <sub>IN</sub> = GND to V <sub>cc</sub>	—	5	—	5	μA
I <sub>LOL</sub>	Output Leakage Current	V <sub>OUT</sub> = 0V to V <sub>cc</sub> , V <sub>cc</sub> = Max.	—	5	—	5	μA
V <sub>OL</sub>	Output Low Voltage	I <sub>OL</sub> = 8mA, V <sub>cc</sub> = Min.	—	0.4	—	0.4	V
V <sub>OH</sub>	Output High Voltage	I <sub>OH</sub> = -4mA, V <sub>cc</sub> = Min.	2.4	—	2.4	—	V
I <sub>CC</sub>	Operating Power Supply Current	V <sub>cc</sub> = Max., $\overline{CE} \leq V_{IL}$ , f = f <sub>MAX</sub> , Outputs Open	—	850	—	1000	mA
I <sub>SB</sub>	Standby Power Supply Current	V <sub>cc</sub> = Max., $\overline{CE} \geq V_{IH}$ , f = f <sub>MAX</sub> , Outputs Open	—	120	—	400	mA
I <sub>SB1</sub>	Full Standby Power Supply Current	V <sub>cc</sub> = Max., $\overline{CE} \geq V_{cc} - 0.2V$ , f = 0, V <sub>IN</sub> ≤ 0.2V or V <sub>IN</sub> ≥ V <sub>cc</sub> - 0.2V, Outputs Open	—	10	—	180	mA

3058 tbl 07

**AC TEST CONDITIONS – IDT7MPV6179/89**

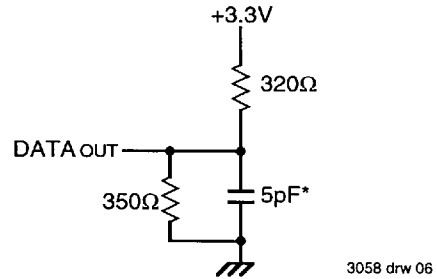
Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	See Figures 1 and 2

3058 tbl 08



\*including scope and jig capacitances

**Figure 1. Output Load**



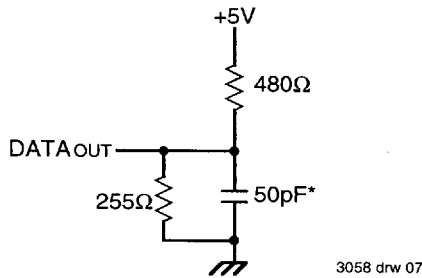
\*including scope and jig capacitances

**Figure 2. Output Load**  
(for tOHZ, tCHZ, tOLZ and tCLZ)

**AC TEST CONDITIONS – IDT7MP6181/82**

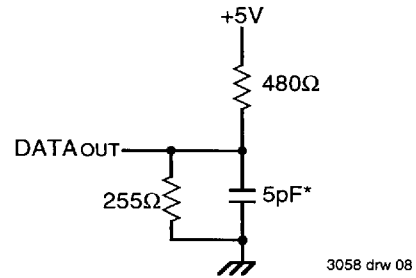
Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	See Figures 3 and 4

3058 tbl 09



\*including scope and jig capacitances

**Figure 3. Output Load**

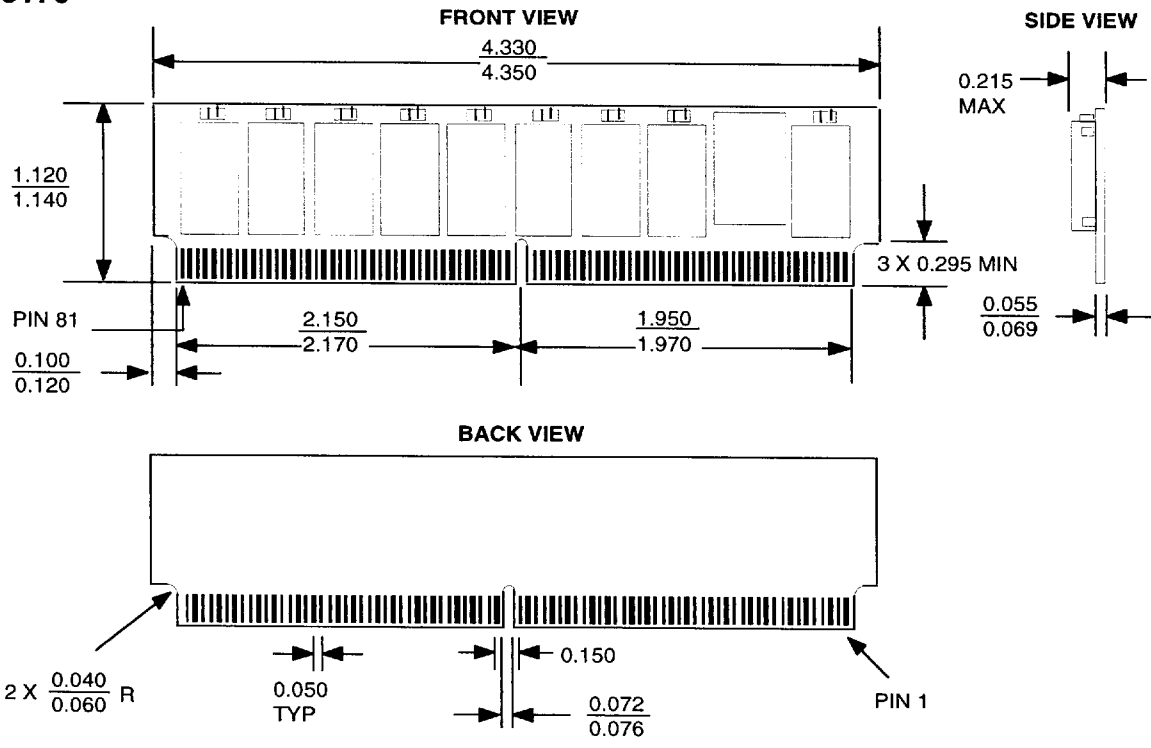


\*including scope and jig capacitances

**Figure 4. Output Load**  
(for tOHZ, tCHZ, tOLZ and tCLZ)

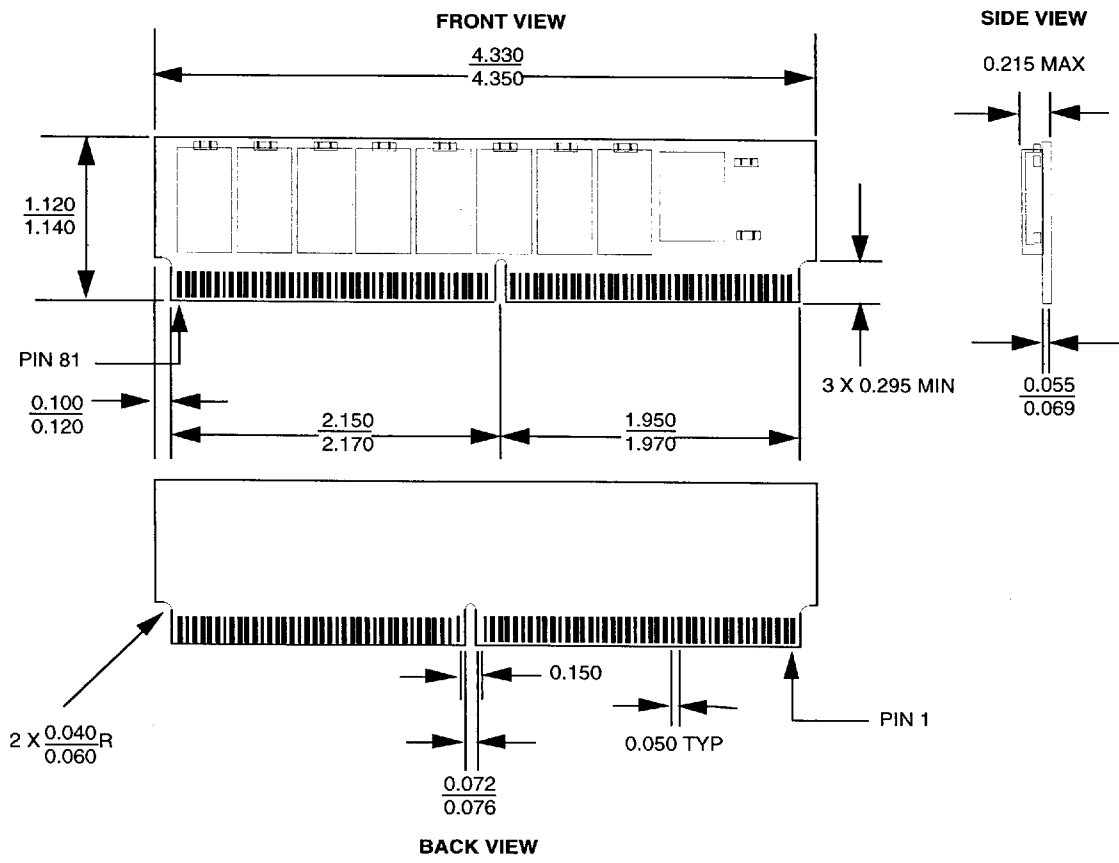
**PACKAGE DIMENSIONS**

**IDT7MPV6179**



3058 drw 09

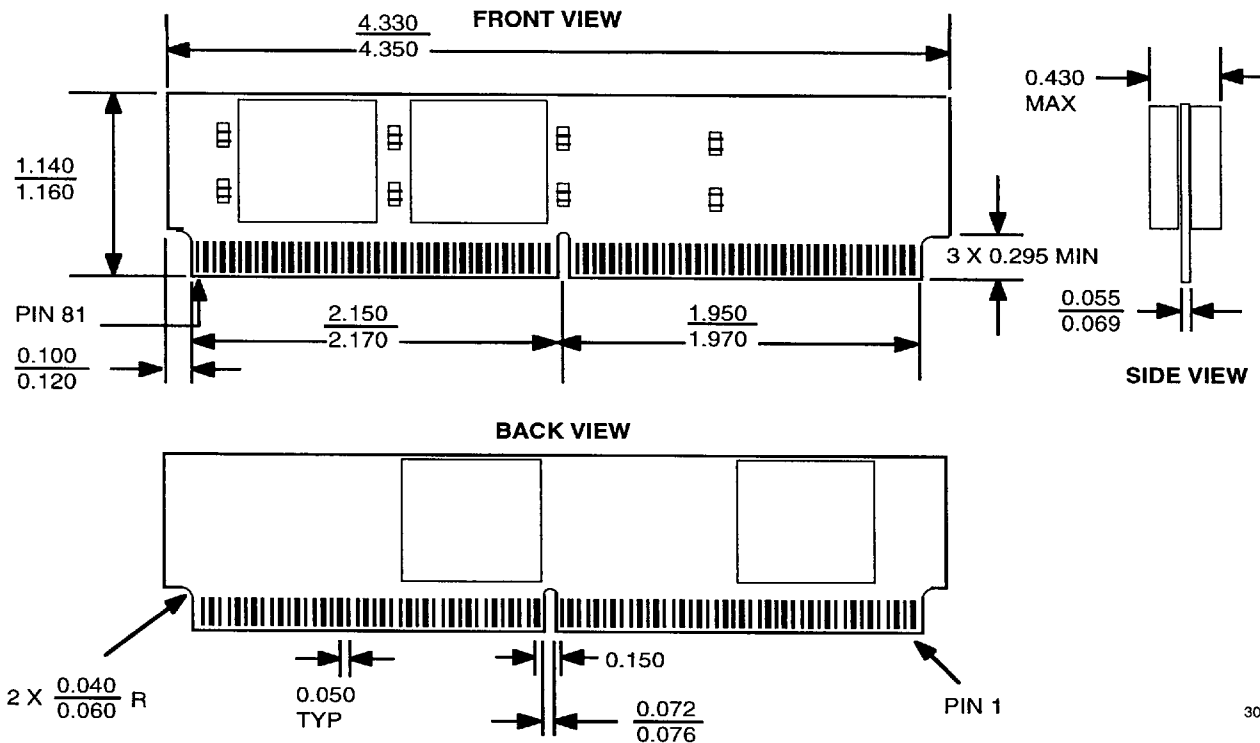
**IDT7MPV6189**



3058 drw 10

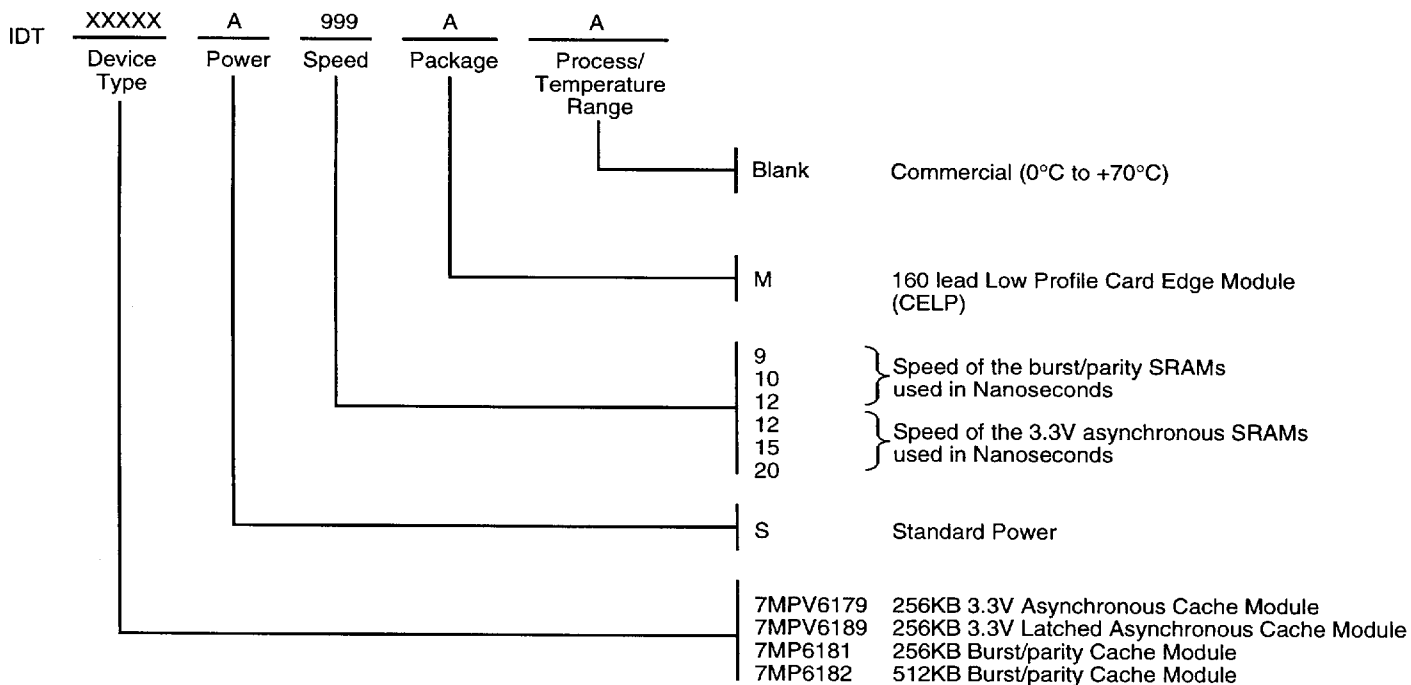
4825771 0021708 320

**IDT7MP6181/82**



3058 drw 11

**ORDERING INFORMATION**



3058 drw 12

Integrated Device Technology, Inc. reserves the right to make changes to the specification in this data sheet in order to improve design or performance and to supply the best possible product.

**Integrated Device Technology, Inc.**

2975 Stender Way, Santa Clara, CA 95052-8015

Telephone: (408) 727-6116

FAX 408-492-8674

4825771 0021709 267